BLC9G24XS-170AV

Power LDMOS transistor

AMPLEON

Rev. 3 — 24 May 2017

Product data sheet

1. Product profile

1.1 General description

170 W LDMOS packaged asymmetrical Doherty power transistor for base station applications at frequencies from 2300 MHz to 2400 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in the Doherty demo board.

Test signal	f	V _{DS}	P _{L(AV)}	Gp	ησ	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	2300 to 2400	30	28	15.5	47	-30 <u>[1]</u>

^[1] Test signal: 3GPP test model 1; 1 to 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

RF power amplifier for W-CDMA base stations and multi carrier applications in the 2300 MHz to 2400 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
1	drain1 (main)			
2	drain2 (peak)			1, 5
3	gate1 (main)			3_
4	gate2 (peak)		7	7
5	video decoupling (main)			4
6	video decoupling (peak)		3 4	2, 6
7	source	[1]		aaa-007731

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	ackage					
	Name	Description	Version				
BLC9G24XS-170AV	-	air cavity plastic earless flanged package; 6 leads	SOT1275-1				

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{\text{th(j-case)}}$	thermal resistance from junction to case	T _{case} = 80 °C; I _{Dq} = 100 mA; V _{GS(amp) peak} = 1 V		
		P _L = 28 W	0.247	K/W
		P _L = 44.5 W	0.197	K/W

6. Characteristics

Table 6. DC characteristics

 T_i = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice		-	1	1	
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.6\text{mA}$	65	-	76.5	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 60 mA	1.5	2.0	2.5	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 300 mA	1.65	2.15	2.65	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 32 V	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	12.1	-	A
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	140	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 3000 mA	-	4.56	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 2.1 \text{ A}$	-	237.5	385	mΩ
Peak dev	vice					
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.9 \text{ mA}$	65	-	76.5	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 90 mA	1.5	2.0	2.5	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 450 mA	1.65	2.15	2.65	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 32 V	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	17.9	-	A
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	140	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 4500 mA	-	6.72	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 3.15 \text{ A}$	-	158	260	mΩ

Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; f_1 = 2300 MHz; f_2 = 2400 MHz; RF performance at V_{DS} = 30 V; I_{Dq} = 250 mA (main); $V_{GS(amp)peak}$ = 0.65 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 2300 MHz to 2400 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _{L(AV)} = 28 W	14.3	15.5	-	dB
RLin	input return loss	P _{L(AV)} = 28 W	-	-10	-6	dB
η_{D}	drain efficiency	P _{L(AV)} = 28 W	40	45	-	%
ACPR	adjacent channel power ratio	P _{L(AV)} = 28 W	-	-29	-24	dBc

Table 8. RF characteristics

Test signal: pulsed CW; t_p = 100 μ s; δ = 10 %; f = 2400 MHz; RF performance at V_{DS} = 30 V; I_{Dq} = 250 mA (main); $V_{GS(amp)peak}$ = 0.65 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 2300 MHz to 2400 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P _{L(3dB)}	output power at 3 dB gain compression		134	157	-	W

Test information

Ruggedness in Doherty operation

The BLC9G24XS-170AV is capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 30 \text{ V}$; I_{Dq} = 150 mA (main); $V_{GS(amp)peak}$ = 0.7 V; P_L = 110 W (CW); f = 2300 MHz.

7.2 Impedance information

Table 9. Typical impedance of main device Measured load-pull data of main device; $I_{Dq} = 300 \text{ mA (main)}$; $V_{DS} = 30 \text{ V}$.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]					
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)					
Maximum po	Maximum power load									
2300	3.1 – j10.0	3.5 – j6.7	88	58.6	17.8					
2350	3.8 – j8.5	3.0 – j6.8	87	57.1	18.1					
2400	8.3 – j11.9	3.2 – j6.7	87	57.4	18.2					
Maximum dra	nin efficiency load									
2300	3.1 – j10.0	6.0 – j5.2	61	66	19.5					
2350	3.8 – j8.5	4.9 – j4.7	62	65.4	20.2					
2400	8.3 – j11.9	5.2 – j4.3	63	64	20.4					

^[1] Z_S and Z_L defined in Figure 1.

Table 10. Typical impedance of peak device

Measured load-pull data of peak device; I_{Dq} = 540 mA (peak); V_{DS} = 30 V.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]						
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)						
Maximum pov	Maximum power load										
2300	4.2 – j11.2	4.5 – j6.4	124	58.7	18.3						
2350	6.1 – j10.7	4.0 – j6.7	126	58.7	17.8						
2400	8.2 – j13.7	3.8 – j6.4	119	57.5	18.2						
Maximum dra	in efficiency load										
2300	4.2 – j11.2	3.8 – j3.7	102	66	19.7						
2350	6.1 – j10.7	3.7 – j4.4	104	65	19.6						
2400	8.2 – j13.7	3.2 – j4.3	94	64	19.8						

^[1] Z_S and Z_L defined in Figure 1.

^[2] at 3 dB gain compression.

^[2] at 3 dB gain compression.

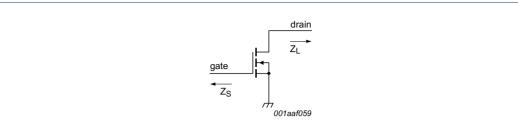


Fig 1. Definition of transistor impedance

7.3 Recommended impedances for Doherty design

Table 11. Typical impedance of main device at 1 : 1 load Measured load-pull data of main device; $I_{Dq} = 300 \text{ mA (main)}$; $V_{DS} = 30 \text{ V}$.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [3]	G _p [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
2300	3.1 – j10.0	4.0 – j5.9	49.2	37.0	18.2
2350	3.8 – j8.5	3.8 – j6.2	49.3	38.0	18.8
2400	8.3 – j11.9	4.0 – j6.3	49.2	38.8	19.0

- [1] Z_S and Z_L defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at $P_{L(AV)} = 44.5 \text{ dBm}$.

Table 12. Typical impedance of main device at 1: 2.5 load

Measured load-pull data of main device; I_{Dq} = 300 mA (main); V_{DS} = 30 V.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [3]	G _p [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
2300	3.1 – j10.0	6.1 – j2.7	47.3	50.1	19.8
2350	3.8 – j8.5	5.5 – j3.4	47.5	50.0	20.5
2400	8.3 – j11.9	4.7 – j2.9	47.3	51.0	20.5

- [1] Z_S and Z_L defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at $P_{L(AV)} = 44.5 \text{ dBm}$.

7.4 VBW in Doherty operation

The BLC9G24XS-170AV shows 100 MHz (typical) video bandwidth in Doherty demo board in 2350 MHz at V_{DS} = 30 V; I_{Dq} = 250 mA and $V_{GS(amp)peak}$ = 0.8 V.

7.5 Test circuit

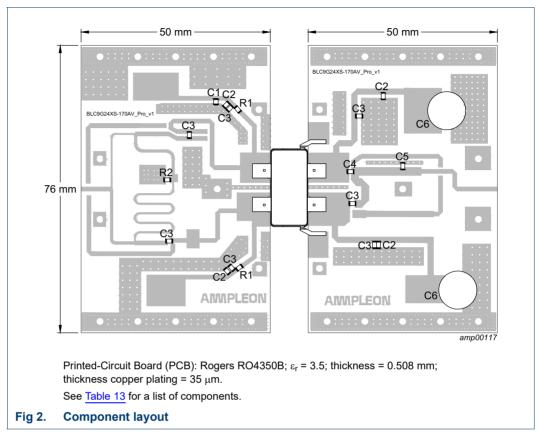


Table 13. List of components

See Figure 2 for component layout.

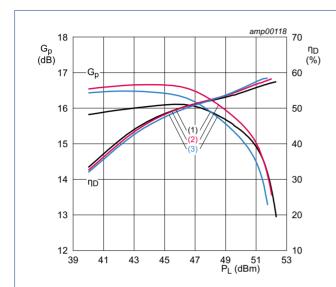
Component	Description Value		Remarks
C1	multilayer ceramic chip capacitor	1 μF, 50 V [1]	Murata
C2	multilayer ceramic chip capacitor	10 μF, 50 V [1]	Murata
C3	multilayer ceramic chip capacitor	11 pF [2]	ATC 600F
C4	multilayer ceramic chip capacitor	8.2 pF [2]	ATC 600F
C5	multilayer ceramic chip capacitor	0.2 pF [2]	ATC 600F
C6	electrolytic capacitor	1000 μF, 100 V	
R1	resistor	5.1 Ω	SMD 0805
R2, R3	resistor	50 Ω	SMD 0805

Murata or capacitor of same quality

American Technical Ceramics type 600F or capacitor of same quality

7.6 Graphical data

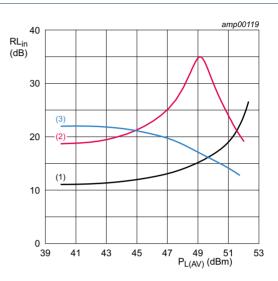
7.6.1 CW



 V_{DS} = 30 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.65 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values

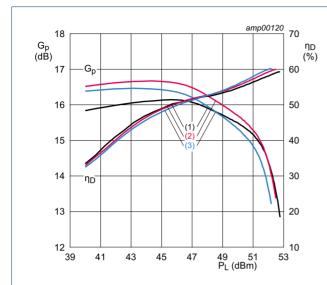


 V_{DS} = 30 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.65 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 4. Input return loss as a function of average output power; typical values

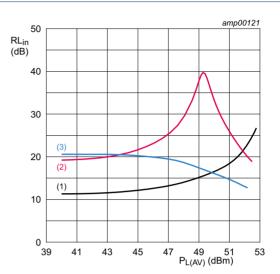
7.6.2 Pulsed CW



 V_{DS} = 30 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.65 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 5. Power gain and drain efficiency as function of output power; typical values

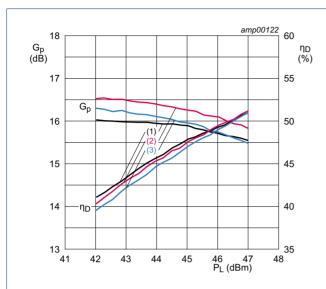


 V_{DS} = 30 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.65 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 6. Input return loss as a function of average output power; typical values

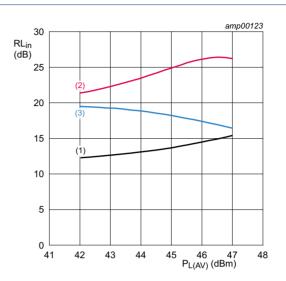
7.6.3 1-Carrier W-CDMA



 V_{DS} = 30 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.65 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

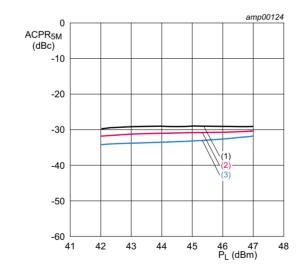
Fig 7. Power gain and drain efficiency as function of output power; typical values



 V_{DS} = 30 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.65 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 8. Input return loss as a function of average output power; typical values

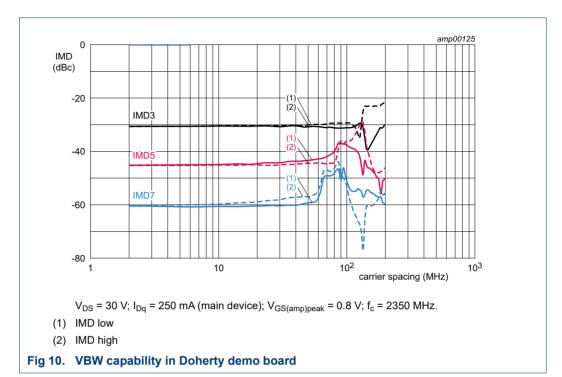


 V_{DS} = 30 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.65 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 9. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

7.6.4 2-Tone VBW



8. Package outline

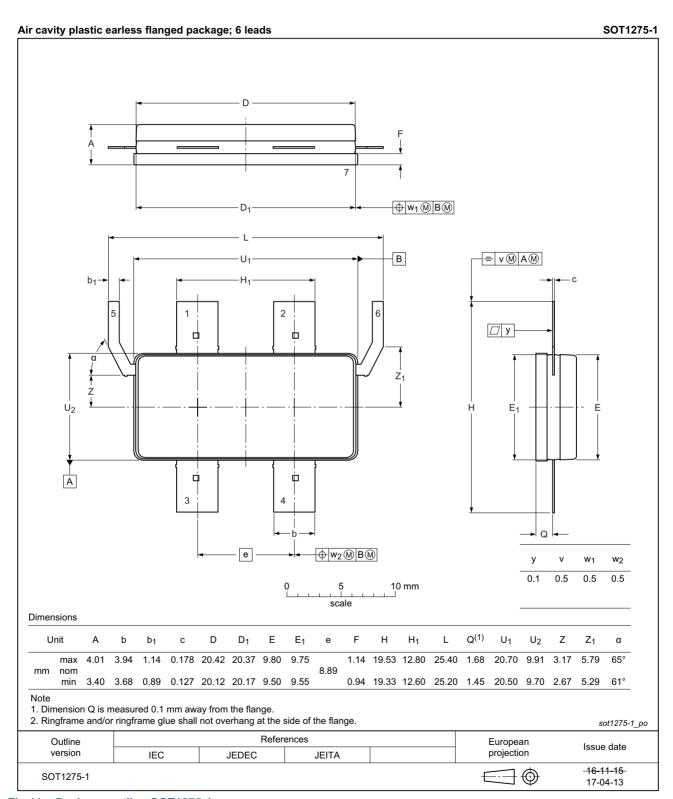


Fig 11. Package outline SOT1275-1

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 14. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

10. Abbreviations

Table 15. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video BandWidth
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC9G24XS-170AV v.3	20170524	Product data sheet	-	BLC9G24XS-170AV v.2
Modifications:	<u>Table 2 on page 2</u> : change simplified outline			
	Table 3 on	page 2: change version to SO	T1275-1	
	Figure 11 on page 11: change package outline drawing to SOT1275-1			T1275-1
BLC9G24XS-170AV v.2	20161220	Product data sheet	-	BLC9G24XS-170AV v.1
BLC9G24XS-170AV v.1	20161021	Product data sheet	-	-

BLC9G24XS-170AV

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12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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